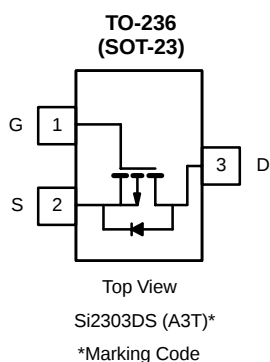


P-Channel, 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^b
-30	0.240 @ $V_{GS} = -10$ V	-1.4
	0.460 @ $V_{GS} = -4.5$ V	-1.0



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	5 sec	Steady State	Unit
Drain-Source Voltage		V _{DS}	−30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C) ^b	T _A = 25 °C	I _D	−1.4	−1.3	A
Pulsed Drain Current ^a		I _{DM}	−10		
Continuous Source Current (Diode Conduction) ^b		I _S	−0.75	−0.6	
Power Dissipation ^b	T _A = 25 °C	P _D	0.9	0.7	W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	−55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}	115	140	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^c		140	175	

Notes

- Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 Board, $t \leq 5$ sec.
- Surface Mounted on FR4 Board.

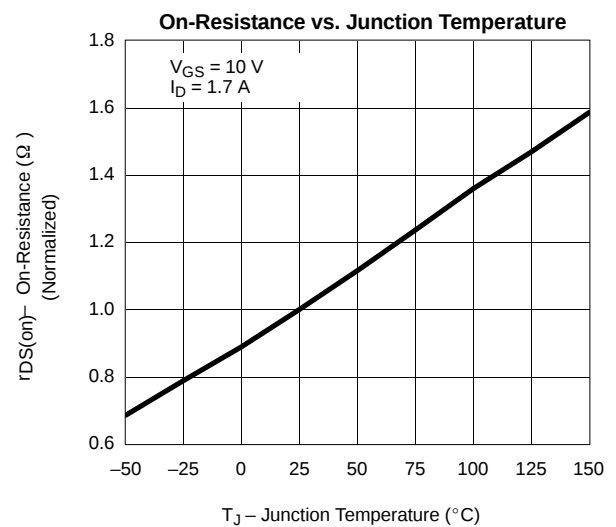
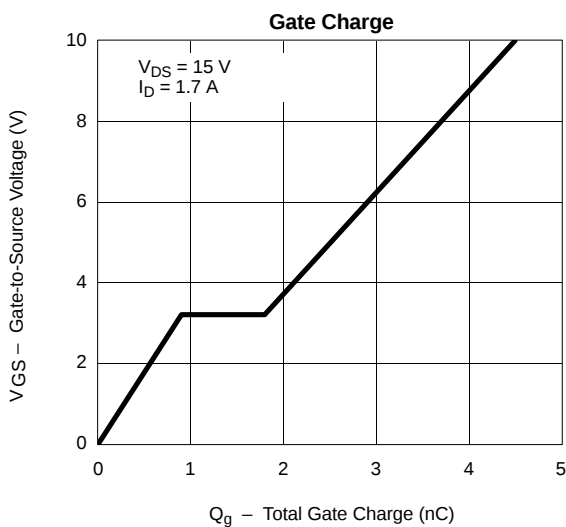
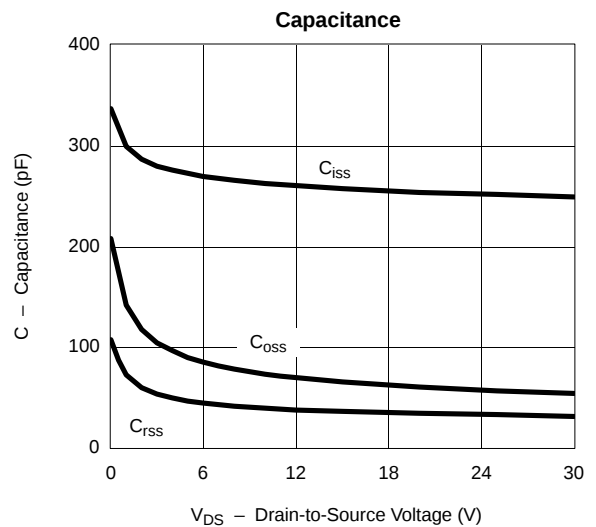
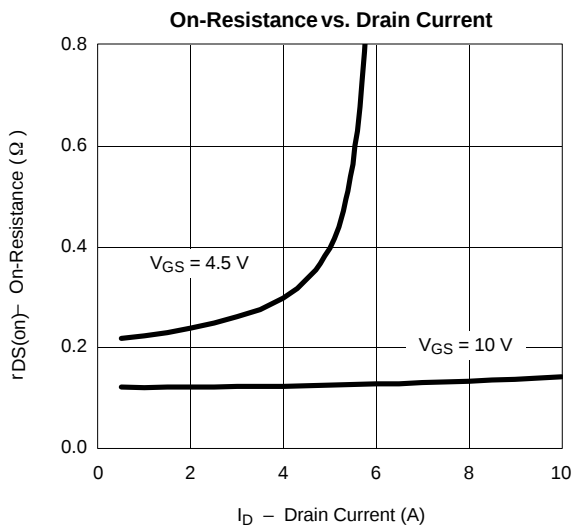
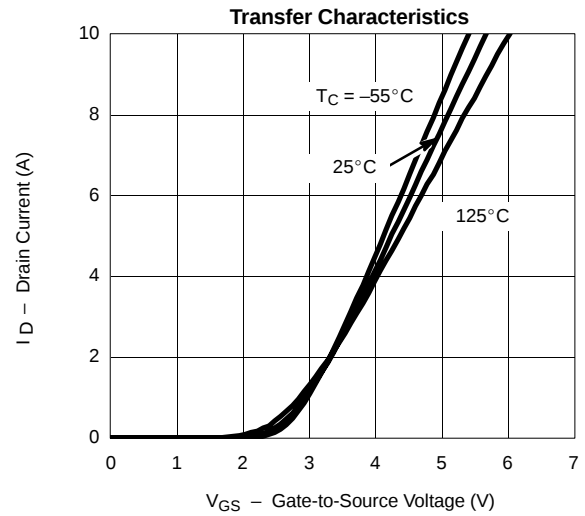
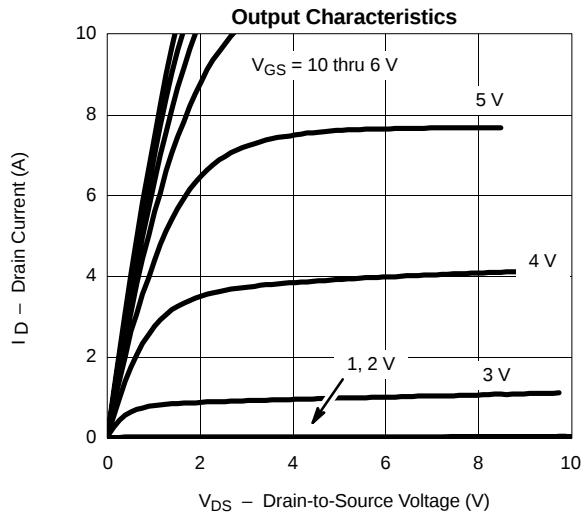


SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = −10 μA	−30			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = −250 μA	−1.0		−3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = −30 V, V _{GS} = 0 V			−1	μA
		V _{DS} = −30 V, V _{GS} = 0 V, T _J = 55 °C			−10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ −5 V, V _{GS} = −10 V	−6			A
Drain-Source On-Resistance ^a	r _{DS(on)}	V _{GS} = −10 V, I _D = −1.7 A		0.120	0.240	Ω
		V _{GS} = −4.5 V, I _D = −1.3 A		0.230	0.460	
Forward Transconductance ^a	g _{fs}	V _{DS} = −5 V, I _D = −1.7 A		2.4		S
Diode Forward Voltage	V _{SD}	I _S = −0.75 A, V _{GS} = 0 V		−0.80	−1.2	V
Dynamic ^b						
Total Gate Charge	Q _g	V _{DS} = −15 V, V _{GS} = −10 V I _D ≅ −1.7 A		4.5	10	nC
Gate-Source Charge	Q _{gs}			0.9		
Gate-Drain Charge	Q _{gd}			0.9		
Input Capacitance	C _{iss}	V _{DS} = −15 V, V _{GS} = 0, f = 1 MHz		260		pF
Output Capacitance	C _{oss}			65		
Reverse Transfer Capacitance	C _{rss}			35		
Switching ^c						
Turn-On Time	t _{d(on)}	V _{DD} = −15 V, R _L = 15 Ω I _D ≅ −1.0 A, V _{GEN} = −4.5 V R _G = 6 Ω		6	20	ns
	t _r			10	20	
Turn-Off Time	t _{d(off)}			15	35	
	t _f			7	20	

Notes

- a. Pulse test: PW ≤ 300 μs duty cycle ≤ 2%.
b. For DESIGN AID ONLY, not subject to production testing.
c. Switching time is essentially independent of operating temperature. • FaxBack 408-970-5600

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

